

ISC Silicon NPN Power Transistor

2SD1171

DESCRIPTION

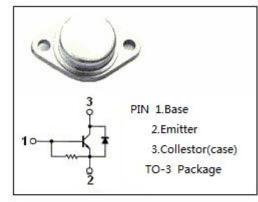
- · High Breakdown Voltage-
 - : V_{CBO}= 1500V (Min)
- · Collector-Emitter Saturation Voltage-
- : V_{CE(sat)}= 4.0V(Max.)@ I_C= 2.0A
- Built-in Damper Diode
- Wide area of safe operation
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

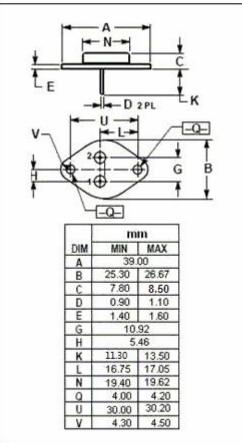
APPLICATIONS

• Designed for horizontal deflection output applications.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
Vсво	Collector-Base Voltage	1500	V
Vces	Collector- Emitter Voltage(V _{BE} = 0)	1500	V
V_{EBO}	Emitter-Base Voltage	6	V
Ic	Collector Current- Continuous	3	А
I _{CP}	Collector Current- Peak	4.5	А
Pc	Collector Power Dissipation @ T _C = 25 °C	50	W
TJ	Junction Temperature	130	$^{\circ}$ C
T _{stg}	Storage Temperature Range	-65~130	$^{\circ}$ C







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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	I _E = 500mA; I _C = 0	5			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 2.0A; I _B = 0.75A			4.0	V
V _{BE} (sat)	Base-Emitter Saturation Voltage	I _C = 2.0A; I _B = 0.75A			1.5	V
Ісво	Collector Base Cutoff Current	V _{CB} =750V; I _E = 0			50	uA
		V _{CB} =1500V; I _E = 0			1	mA
h _{FE}	DC Current Gain	I _C = 2A; V _{CE} = 10V	4		15	
V _{ECF}	C-E Diode Forward Voltage	I _F = 4A			2.5	V
Switching T	imes					

t _{stg}	Storage Time		I _C = 2.5A,I _{B1} = I _{B2} = 0.75A		10	μ \$
t _f	Fall Time				0.8	μS

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